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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of

MARTIN, T. et al.

Atty. Ref.: 124-909

Serial No. 10/009,530

TC/A.U.: 1765

Filed: January 22, 2002

Examiner: Anderson

For: METHOD OF FABRICATING A SEMICONDUCTOR DEVICE

\* \* \* \* \*

August 11, 2004

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

**INFORMATION DISCLOSURE STATEMENT**

Attention is invited to the attached copy of an official communication in the counterpart European application and a copy of each document cited in it. A completed Form PTO-1449 is also attached.

Please take this information into account when further examining this application; a Request for Continued Examination was filed on July 30, 2004.

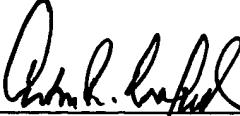
Official citation and consideration of all the attached documents is requested. Please return to the undersigned a copy of the attached PTO-1449 with the examiner's initials in the left column [MPEP §609] with the next communication.

The filing of an Information Disclosure Statement shall not be construed as a representation that a search has been made, an admission that the information cited is, or is considered to be, material to patentability [37 C.F.R. § 1.97(g) & (h)] or that no other material information exists.

The Commissioner is hereby authorized to charge our Deposit Account No. 14-1140 for any fees required in connection with the filing of this Information Disclosure Statement.

Respectfully submitted,

**NIXON & VANDERHYE P.C.**

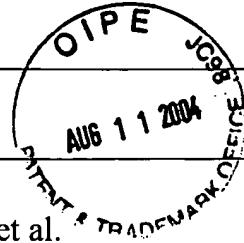
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## INFORMATION DISCLOSURE CITATION

ATTY. DOCKET NO.

124-909

SERIAL NO.

10/009,530

**APPLICANT**

MARTIN, T. et al.

(Use several sheets if necessary)

**FILING DATE**

TC/A.U.

January 22, 2002

1765

## U.S. PATENT DOCUMENTS

## FOREIGN PATENT DOCUMENTS

**OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)**

Tsang; "Selective Area Growth of GaAs and  $in_{0.53}Ga_{0.47}As$  Epilayer Structures by Chemical Beam Epitaxy Using Silicon Shadow Masks: A Demonstration of the Beam Nature", *Appl. Phys. Lett.* **46**(8), 15 April 1985, pages 742-744.

Tsang, "Chemical Beam Epitaxy of InP and GaAs", *Appl. Phys. Lett.* **45**(11), 1 December 1984, pages 1234-1236.

\*Examiner

### Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.